

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _c = +25°C
-60V	50mΩ @ V _{GS} = -10V	-18A
	70mΩ @ V _{GS} = -4.5V	-15A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

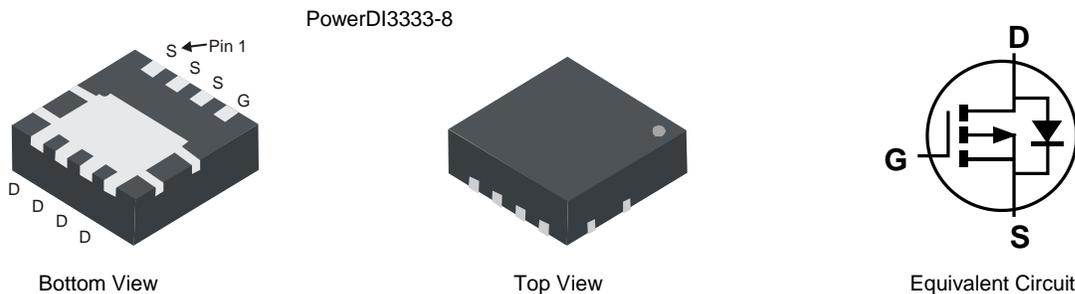
- Backlighting
- Power-management functions
- DC-DC converters

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – ensures on state losses are minimized
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMPH6050SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.034 grams (Approximate)

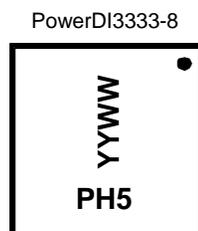


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMPH6050SFGQ-7	PowerDI3333-8	2,000	Tape & Reel
DMPH6050SFGQ-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



PH5= Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 23 = 2023)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-6.1	A
		T _A = +100°C		-4.2	
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	T _C = +25°C	I _D	-18	A
		T _C = +100°C		-12	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-32	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-32	A
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	-24.8	A
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	30.8	mJ

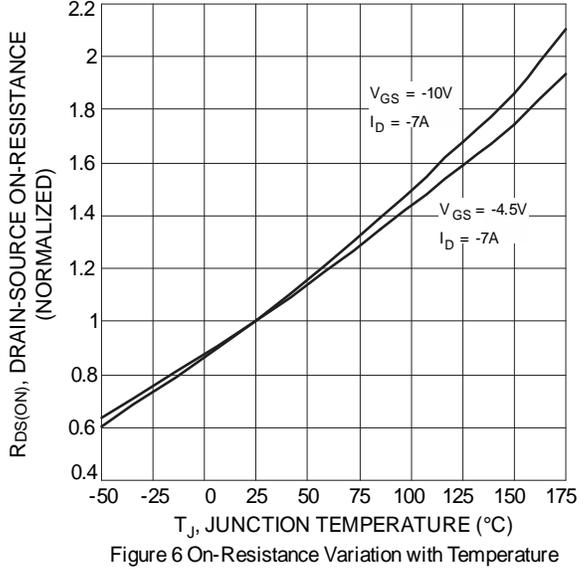
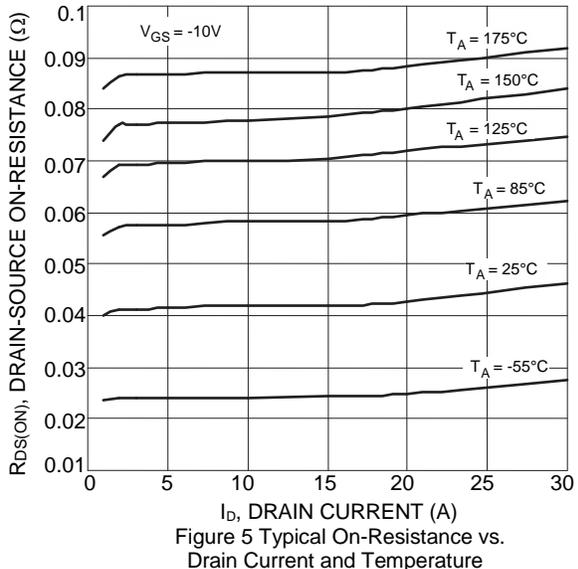
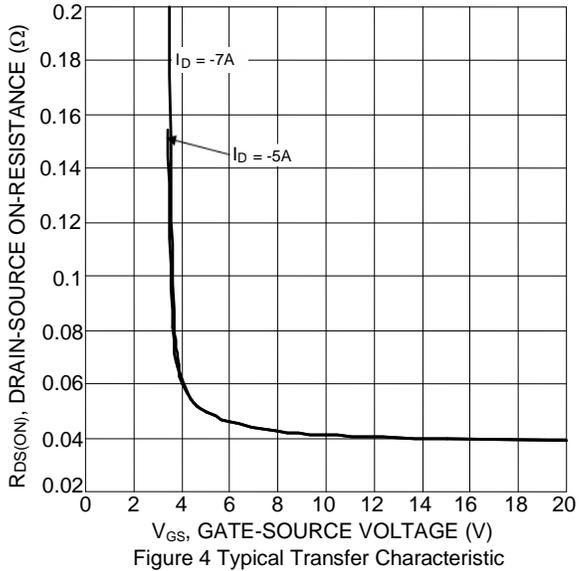
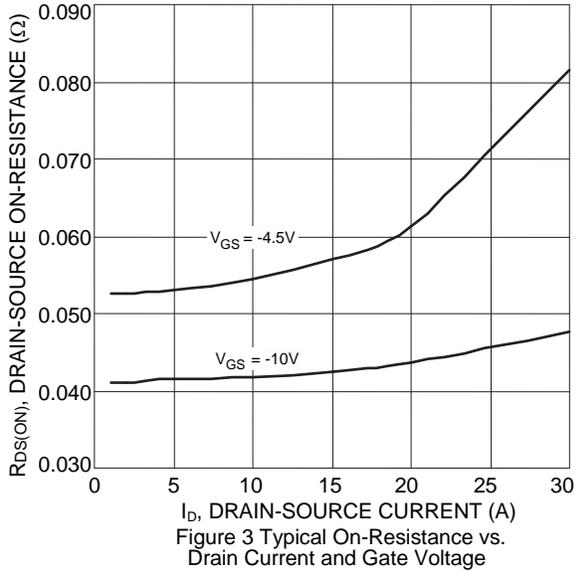
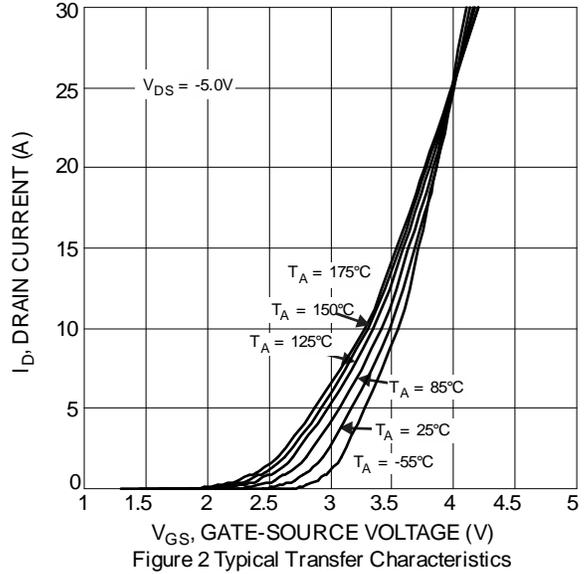
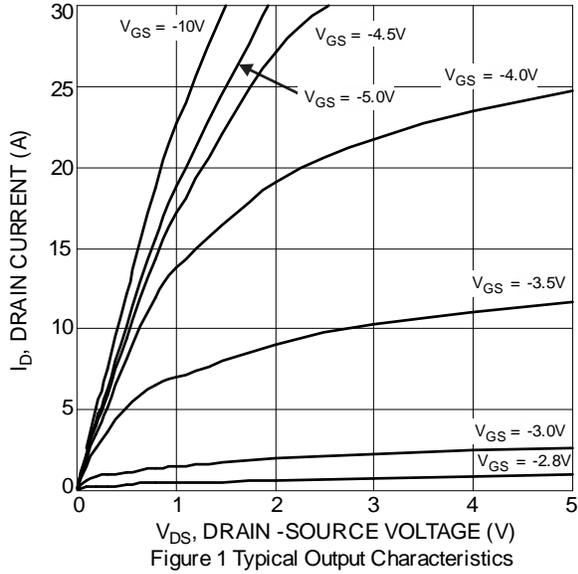
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	125	°C/W
	t < 10s		85	
Total Power Dissipation (Note 6)		P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	54	°C/W
	t < 10s		37	
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	6	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	µA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	41	50	mΩ	V _{GS} = -10V, I _D = -7A
		—	52	70		
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1293	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	86.3	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	64.7	—	pF	
Gate Resistance	R _g	—	12	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	11.9	—	nC	V _{DS} = -30V, I _D = -5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	24.1	—	nC	
Gate-Source Charge	Q _{gs}	—	3.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	5.7	—	nC	
Turn-On Delay Time	t _{d(ON)}	—	4.3	—	ns	V _{DS} = -30V, V _{GS} = -10V, R _G = 3Ω, I _D = -5A
Turn-On Rise Time	t _r	—	6.3	—	ns	
Turn-Off Delay Time	t _{d(OFF)}	—	46.7	—	ns	
Turn-Off Fall Time	t _f	—	25.3	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	13.6	—	ns	I _F = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	7.4	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



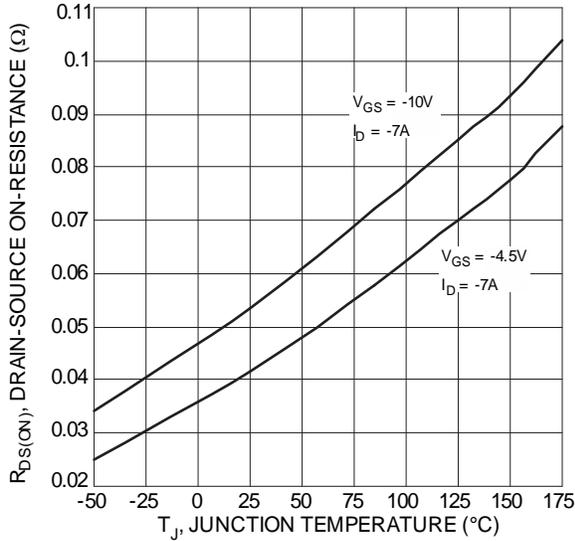


Figure 7 On-Resistance Variation with Temperature

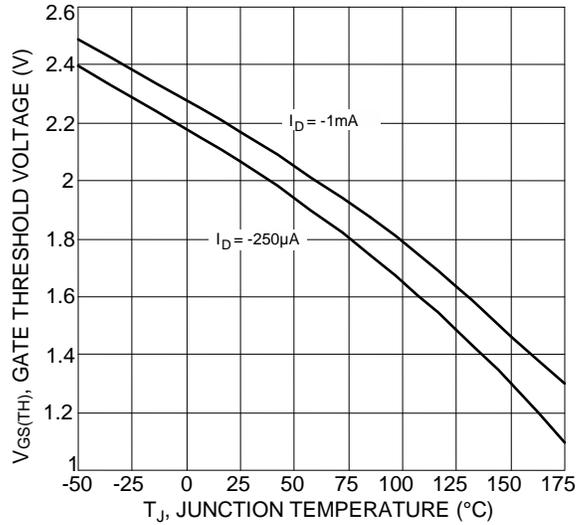


Figure 8 Gate Threshold Variation vs. Junction Temperature

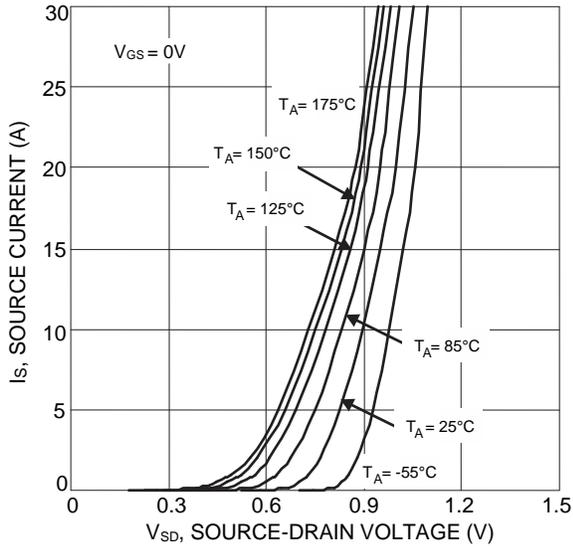


Figure 9 Diode Forward Voltage vs. Current

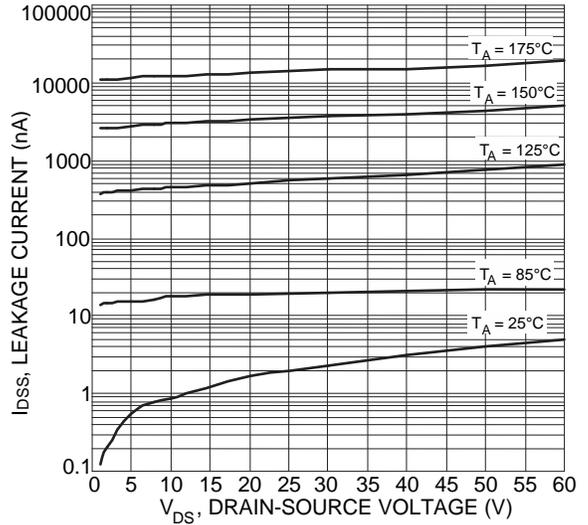


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

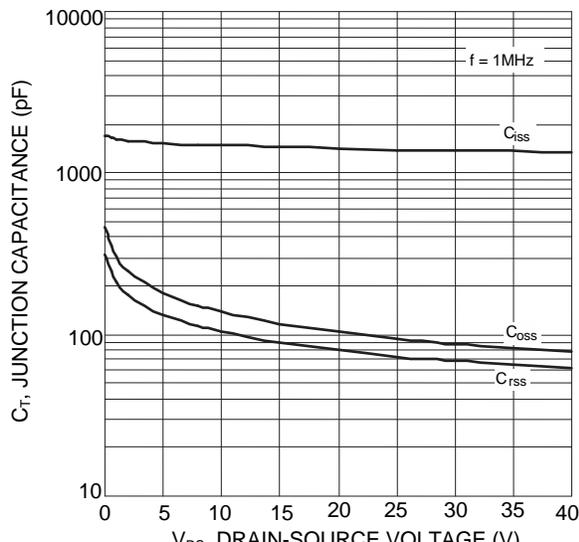


Figure 11 Typical Junction Capacitance

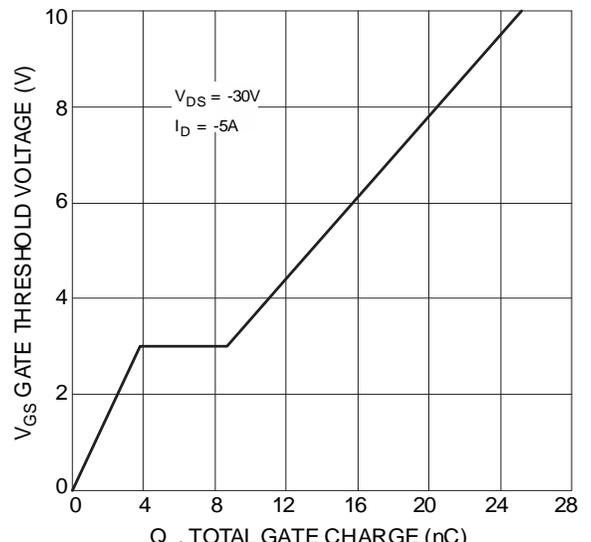
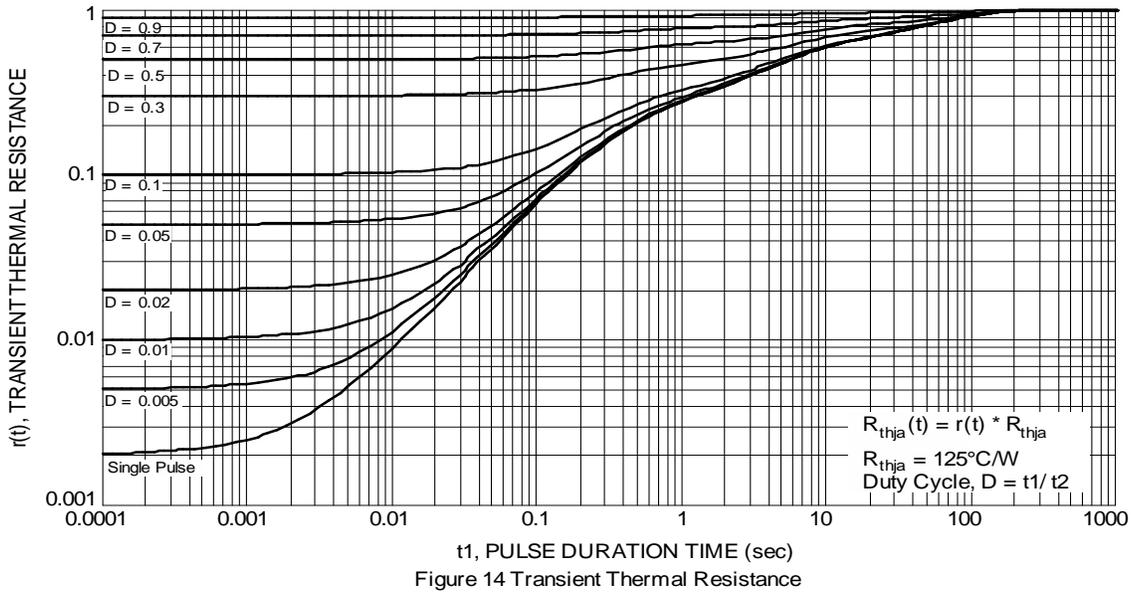
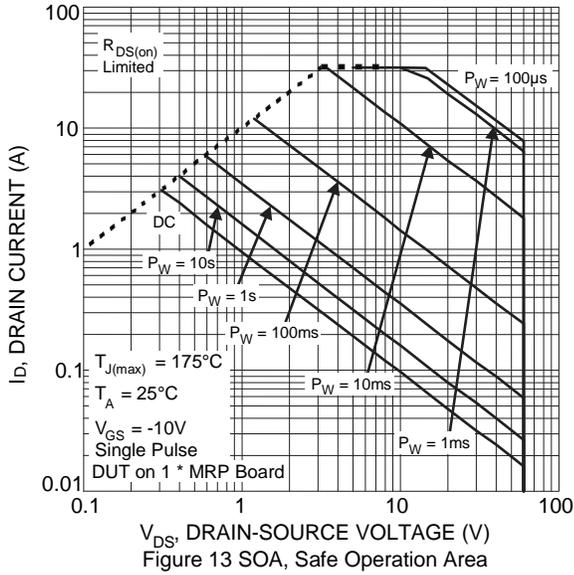


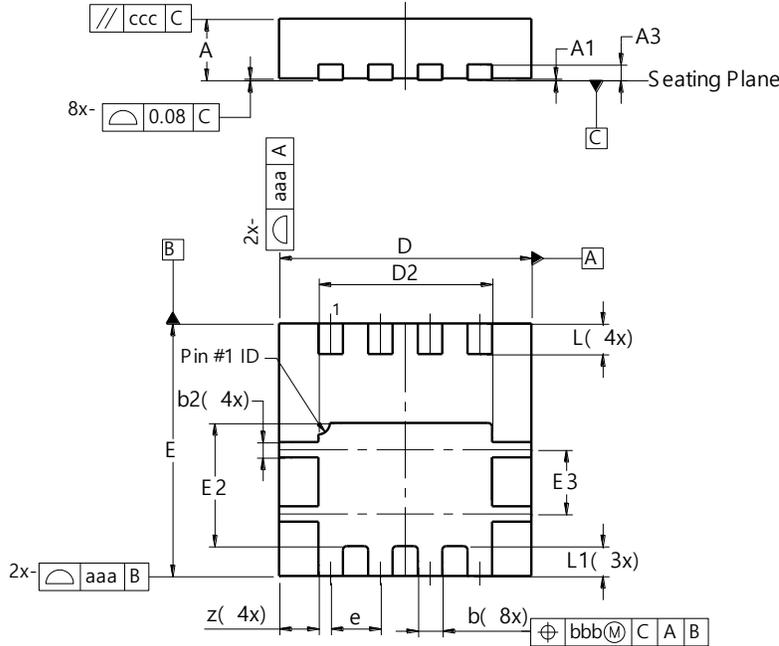
Figure 12 Gate Charge



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

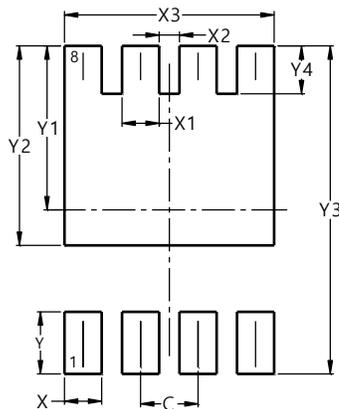


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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